What is claimed is:

1. A semiconductor device, comprising:

a first active fin extending in a first direction on a substrate, the first active fin comprising a first straight line extension portion, a second straight line extension portion, and a bent portion between the first and second straight line extension portions;

a second active fin extending in the first direction on the substrate; and

a gate structure extending in a second direction perpendicular to the first direction on the substrate, the gate structure crossing one of the first and second straight line extension portions of the first active fin and crossing the second active fin; and

wherein the bent portion extends in an oblique direction with respect to the first direction between adjacent ends of the first and second straight line extension portions;

wherein the bent portion includes a first bent portion and a second bent portion contacting respective opposite ends in the first direction of the first straight line extension portion, and

wherein the first and second bent portions are symmetric with respect to each other.

2. The semiconductor device of claim 1,

wherein each of the first and second straight line extension portions extends in the first direction, and

wherein the first straight line extension portion is offset in the second direction from the second straight line extension portion by the bent portion.

3. The semiconductor device of claim 1 or claim 2, wherein the first straight line extension portion is closer to a central portion of the gate structure in the second direction than the second straight line extension portion due to the bent portion.

4. The semiconductor device of any of claims 1 to 3,

wherein the second active fin includes a plurality of second active fins spaced apart from each other in the first direction, and

wherein each of the plurality of second active fins has a straight line shape.

5. The semiconductor device of any of claims 1 to 4, wherein the second active fin has a straight line shape.

6. The semiconductor device of any of claims 1 to 3,

wherein the second active fin includes a plurality of second active fins spaced apart from each other in the first direction, and

wherein each of the plurality of second active fins comprises a third straight line extension portion, a fourth straight line extension portion, and a second bent portion between the third and fourth straight line extension portions.

7. The semiconductor device of claim 6,

wherein the gate structure crosses the second bent portion, and

wherein the second bent portion extends in a bending direction that is substantially the same as a bending direction of the bent portion of the first active fin in the second direction.

8. The semiconductor device of any of claims 1 to 7, further comprising:

an insulating interlayer on the substrate that covers the first and second active fins, the insulating interlayer including an opening crossing the first and second active fins,

wherein the gate structure is in the opening.

9. The semiconductor device of claim 8, wherein sidewalls and upper surfaces of portions of the first and second active fins are exposed by the opening.

10. The semiconductor device of any of claims 1 to 9,

wherein the gate structure includes a gate insulation layer, a gate electrode and a capping pattern, the gate electrode including a metal, and

wherein the gate insulation layer surrounds sidewalls and a bottom of the gate electrode.

11. A semiconductor device, comprising:

a first active fin extending in a first direction on a substrate, the first active fin comprising a first straight line extension portion, a second straight line extension portion, and a first bent portion between the first and second straight line extension portions;

a plurality of second active fins extending in the first direction on the substrate, the plurality of second active fins being spaced apart from each other in the first direction;

a plurality of third active fins extending in the first direction on the substrate, the plurality of third active fins being spaced apart from each other in the first direction, wherein the plurality of third active fins are not aligned with the plurality of second active fins in a second direction perpendicular to the first direction;

a fourth active fin extending in the first direction on the substrate, the fourth active fin comprising a third straight line extension portion, a fourth straight line extension portion, and a second bent portion between the third and fourth straight line extension portions;

a first gate structure crossing the first straight line extension portion;

a second gate structure crossing the second straight line extension portion and one of the plurality of second active fins;

a third gate structure crossing one of the third active fins and the third straight line extension portion; and

a fourth gate structure crossing the fourth straight line extension portion;

wherein the first bent portion extends in an oblique direction with respect to the first direction between adjacent ends of the first and second straight line extension portions;

wherein the first bent portion includes a third bent portion and a fourth bent portion contacting respective opposite ends in the first direction of the first straight line extension portion, and

wherein the third and fourth second bent portions are symmetric with respect to each other; and

wherein the second bent portion extends in an oblique direction with respect to the first direction between adjacent ends of the third and fourth straight line extension portions;

wherein the second bent portion includes a fifth bent portion and a sixth bent portion contacting respective opposite ends in the first direction of the third straight line extension portion, and

wherein the fifth and sixth bent portions are symmetric with respect to each other.

12. The semiconductor device of claim 11,

wherein the first straight line extension portion is closer to a central portion of the first gate structure in the second direction than the second straight line extension portion, and

wherein the second straight line extension portion is closer to a central portion of the second gate structure in the second direction than the first straight line extension portion.

13. The semiconductor device of claim 11 or claim 12,

wherein the third straight line extension portion is closer to a central portion of the third gate structure in the second direction than the fourth straight line extension portion, and

wherein the fourth straight line extension portion is closer to a central portion of the fourth gate structure in the second direction than the third straight line extension portion.

14. The semiconductor device of any of claims 11 to 13, wherein each of the plurality of second active fins and each of the plurality of third active fins has a straight line shape.

15. The semiconductor device of any of claims 11 to 13,

wherein each of the plurality of second active fins includes a fifth straight line extension portion, a sixth straight line extension portion, and a seventh bent portion between the fifth and sixth straight line extension portions,

wherein each of the plurality of third active fins includes a seventh straight line extension portion, an eighth straight line extension portion, and a eighth bent portion between the seventh and eighth straight line extension portions,

wherein the second gate structure crosses the seventh bent portion of one of the plurality of second active fins, and

wherein the third gate structure crosses the eighth bent portion of one of the plurality of third active fins.

16. The semiconductor device of claim 15,

wherein the first and seventh bent portions are substantially parallel to each other, and

wherein the second and eighth bent portions are substantially parallel to each other.

17. A semiconductor device, comprising:

a first active fin extending in a first direction on a substrate, the first active fin comprising a first straight line extension portion, a second straight line extension portion, and an oblique portion connecting the first and second straight line extension portions;

a second active fin extending in the first direction on the substrate parallel to the first and second straight line extension portions of the first active fin; and

a first gate structure and a second gate structure each extending in a second direction perpendicular to the first direction on the substrate, the first and second gate structures each crossing the first and second active fins,

wherein the oblique portion extends in a third direction that is oblique with respect to the first and second directions such that a first distance in the second direction between a first portion of the first active fin between the first and second gate structures and the second active fin is greater than a second distance in the second direction between a second portion of the first active fin not between the first and second gate structures and the second active fin; and

wherein the oblique portion includes a first oblique portion and a second oblique portion contacting respective opposite ends of the first straight line extension portion, and

wherein the first and second oblique portions are symmetric with respect to each other.

18. The semiconductor device of claim 17,

wherein each of the first and second straight line extension portions extends in the first direction,

wherein the first straight line extension portion is not collinear with the second straight line extension portion, and

wherein the oblique portion extends in the third direction between adjacent ends of the first and second straight line extension portions in the first direction.